



SiC SCHOTTKY DIODE TYPE 2×50A

Preliminary

Features

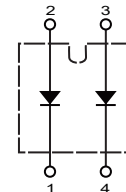
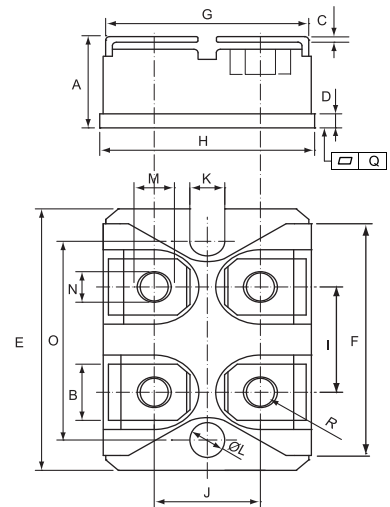
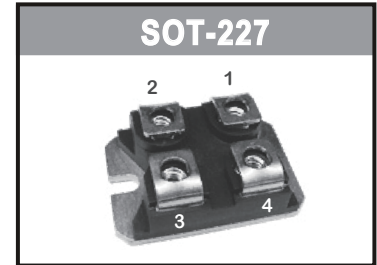
- High surge current capable
- Zero reverse recovery current
- High bandwidth
- Isolation type package
- Temperature Independent Switching Behavior
- VDC 650 V
- I<sub>F</sub> (T<sub>C</sub><135°C) 2×50 A

Benefits

- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices without thermal runaway

Applications

- Motor drives
- Switch mode power supplies
- Ev chargers
- Solar inverters
- Welding equipment
- Power factor correction
- Diode snubber
- Automotive
- induction heating



parallel

	DIMENSIONS			
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	0.460	0.483	11.68	12.28
B	0.307	0.323	7.80	8.20
C	0.030	0.033	0.75	0.85
D	0.071	0.081	1.80	2.05
E	1.488	1.504	37.80	38.20
F	1.248	1.260	31.70	32.00
G	0.917	0.957	23.30	24.30
H	0.996	1.008	25.30	25.60
I	0.579	0.602	14.70	15.30
J	0.492	0.516	12.50	13.10
K	0.161	0.169	4.10	4.30
L	0.161	0.169	4.10	4.30
M	0.181	0.197	4.60	5.00
N	0.165	0.181	4.20	4.60
O	1.181	1.197	30.00	30.40
Q	-0.002	0.004	-0.05	0.10
R	M4*8			

Maximum Ratings

Operating Junction Temperature : - 55 °C to +175 °C

Storage Temperature : -55 °C to +175 °C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
CSRI2×50-065P2B	650V	650V

Maximum Rating	Symbol	Conditions	Value	Unit
Continuous forward current (per diode)	I <sub>F</sub>	T <sub>C</sub> =135 °C	50	A
Surge non-repetitive forward current sine halfwave (per diode)	I <sub>FSM</sub>	T <sub>C</sub> =25 °C, t <sub>p</sub> =8.3 ms	400	
		T <sub>C</sub> =150 °C, t <sub>p</sub> =8.3 ms	250	
Non-repetitive peak forward current (per diode)	I <sub>F,max</sub>	T <sub>C</sub> =25 °C, t <sub>p</sub> =10 μs	1600	
		T <sub>C</sub> =150 °C, t <sub>p</sub> =10 μs	1000	
Repetitive peak reverse voltage	V <sub>RRM</sub>	T <sub>J</sub> =25 °C	650	V
Isolation voltage between All Terminals and Baseplate	V <sub>iso</sub>	50/60 Hz, t=1min I <sub>ISOL</sub> ≤ 1mA	2500	V
Mounting torque		To heatsink	1.3	Nm
		To terminal	1.1	



**Electrical Characteristics**, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified. (per diode)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	$V_{DC}$		650	-	-	V
Diode forward voltage	$V_F$	$I_F=50\text{A}, T_j=25\text{ }^\circ\text{C}$	-	1.50	1.70	
		$I_F=50\text{A}, T_j=175\text{ }^\circ\text{C}$	-	1.70	2.00	
Reverse current	$I_R$	$V_R=650\text{V}, T_j=25\text{ }^\circ\text{C}$	-	30	60	$\mu\text{A}$
		$V_R=650\text{V}, T_j=175\text{ }^\circ\text{C}$	-	60	250	

**AC Characteristics** (per diode)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Total capacitive charge	$Q_{rr}$	$V_R=400\text{V}, T_j=25\text{ }^\circ\text{C}$	-	110	-	nC
Total capacitance	C	$V_R=0\text{V}, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	1590	-	pF
		$V_R=200\text{V}, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	232	-	
		$V_R=400\text{V}, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	229	-	

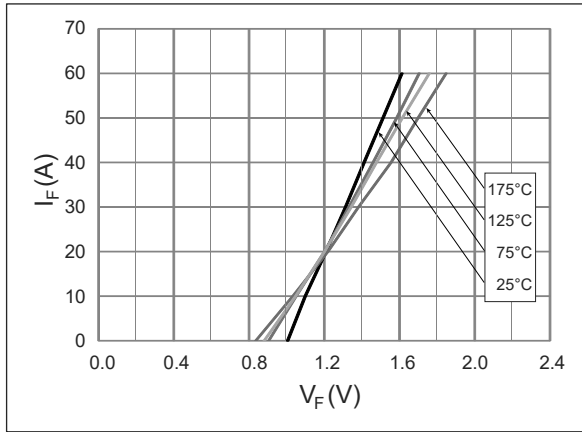
**Thermal Characteristics** (per diode)

Static Characteristics	Symbol	Values	Unit
		typ.	
Thermal resistance from junction to case	$R_{\theta JC}$	0.28	$^\circ\text{C/W}$

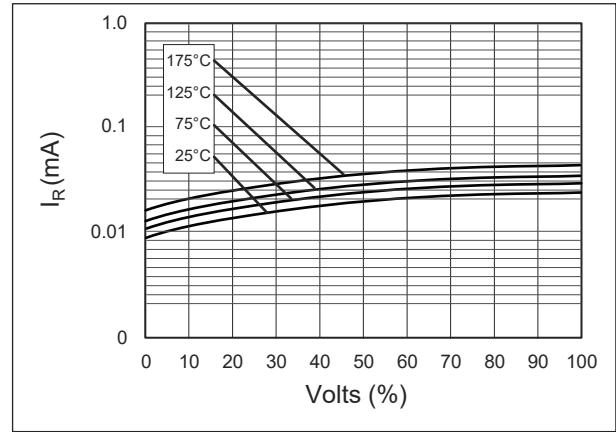


Typical Performance

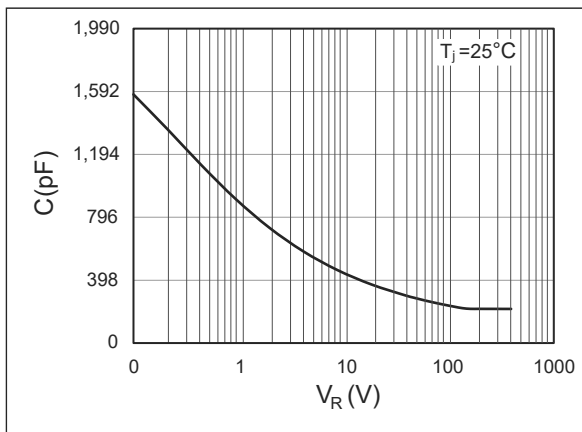
Forward Characteristics (parameterized on  $T_j$ )



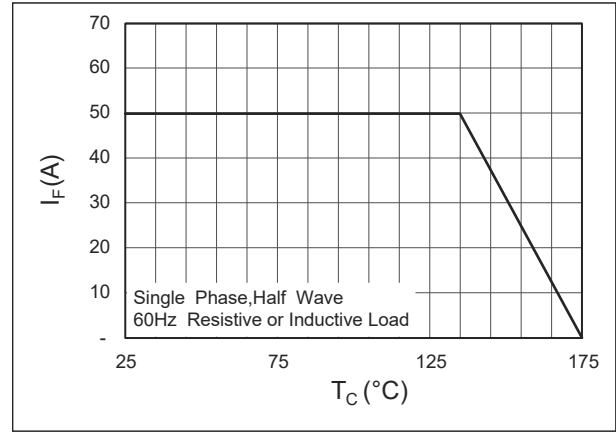
Reverse Characteristics (parameterized on  $T_j$ )



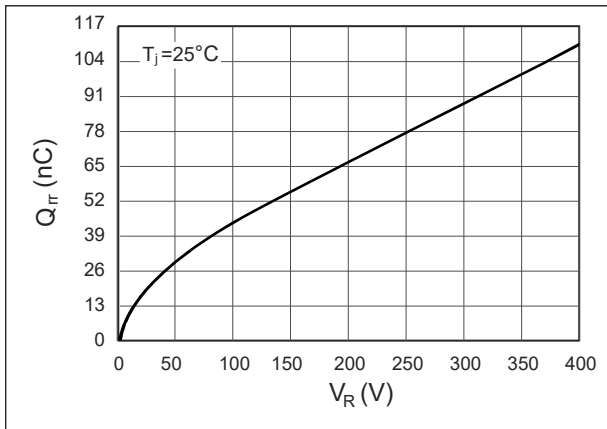
Capacitance



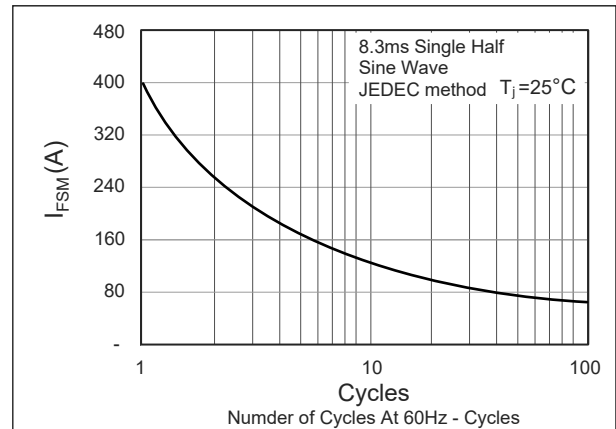
Current Derating



Recovery Charge



Forward Surge Current





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